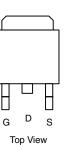
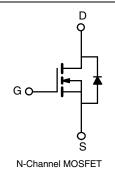


Automotive N-Channel 60 V (D-S) 175 °C MOSFET

| PRODUCT SUMMARY | | | | | | |
|--|--------|--|--|--|--|--|
| V _{DS} (V) | 60 | | | | | |
| $R_{DS(on)}(\Omega)$ at $V_{GS} = 10 V$ | 0.0035 | | | | | |
| $R_{DS(on)}(\Omega)$ at $V_{GS} = 4.5 V$ | 0.0039 | | | | | |
| I _D (A) | 120 | | | | | |
| Configuration | Single | | | | | |

TO-263





FEATURES

- TrenchFET[®] Power MOSFET
- Package with Low Thermal Resistance
- AEC-Q101 Qualified^d
- 100 % $\rm R_g$ and UIS Tested
- Material categorization: For definitions of compliance please see <u>www.vishay.com/doc?99912</u>



| ORDERING INFORMATION | | | | |
|---------------------------------|--------------------|--|--|--|
| Package | TO-263 | | | |
| Lead (Pb)-free and Halogen-free | SQM120N06-3m5L-GE3 | | | |

| ABSOLUTE MAXIMUM RATINGS ($T_c = 25 \degree C$, unless otherwise noted) | | | | | | |
|--|-------------------------|-----------------------------------|-------------|------|--|--|
| PARAMETER | | SYMBOL | LIMIT | UNIT | | |
| Drain-Source Voltage | | V _{DS} | 60 | M | | |
| Gate-Source Voltage | | V _{GS} | ± 20 | V | | |
| Continuous Drain Current ^a | T _C = 25 °C | 1 | 120 | | | |
| | T _C = 125 °C | l I _D | 120 | | | |
| Continuous Source Current (Diode Conduction) ^a | I _S | 120 | А | | | |
| Pulsed Drain Current ^b | I _{DM} | 480 | | | | |
| Single Pulse Avalanche Current | L = 0.1 mH | I _{AS} | 100 | | | |
| Single Pulse Avalanche Energy | | E _{AS} | 500 | mJ | | |
| Mauinum Daura Diasin atianh | T _C = 25 °C | D | 375 | W | | |
| Maximum Power Dissipation ^b | T _C = 125 °C | P _D | 125 | vv | | |
| Operating Junction and Storage Temperature Ran | ige | T _J , T _{stg} | -55 to +175 | °C | | |

| THERMAL RESISTANCE RATINGS | | | | | | |
|----------------------------|------------------------|-------------------|-------|------|--|--|
| PARAMETER | | SYMBOL | LIMIT | UNIT | | |
| Junction-to-Ambient | PCB Mount ^c | R _{thJA} | 40 | °C/W | | |
| Junction-to-Case (Drain) | | R _{thJC} | 0.4 | 0/10 | | |

Notes

- a. Package limited.
- b. Pulse test; pulse width $\leq 300~\mu s,~duty~cycle \leq 2~\%.$
- c. When mounted on 1" square PCB (FR-4 material).
- d. Parametric verification ongoing.

1

SQM120N06-3m5L



Vishay Siliconix

| PARAMETER | SYMBOL | TES | MIN. | TYP. | MAX. | UNIT | | |
|---|--------------------------|---|---|------|--------|--------|----|--|
| Static | | | | | • | | | |
| Drain-Source Breakdown Voltage | V _{DS} | $V_{GS} = 0, I_D = 250 \ \mu A$ | | 60 | - | - | v | |
| Gate-Source Threshold Voltage | V _{GS(th)} | V _{DS} = | $V_{DS} = V_{GS}$, $I_D = 250 \ \mu A$ | | 2.0 | 2.5 | v | |
| Gate-Source Leakage | I _{GSS} | V _{DS} = | $V_{DS} = 0 V, V_{GS} = \pm 20 V$ | | - | ± 100 | nA | |
| | | $V_{GS} = 0 V$ | V _{DS} = 60 V | - | - | 1 | | |
| Zero Gate Voltage Drain Current | I _{DSS} | $V_{GS} = 0 V$ | $V_{DS} = 60 \text{ V}, \text{ T}_{J} = 125 ^{\circ}\text{C}$ | - | - | 50 | μA | |
| | | $V_{GS} = 0 V$ | $V_{DS} = 60 \text{ V}, \text{ T}_{J} = 175 ^{\circ}\text{C}$ | - | - | 900 | 1 | |
| On-State Drain Current ^a | I _{D(on)} | $V_{GS} = 10 V$ | $V_{DS} \ge 5 V$ | 120 | - | - | Α | |
| | | $V_{GS} = 10 V$ | I _D = 30 A | - | 0.0028 | 0.0035 | | |
| Drain-Source On-State Resistance ^a | Р | $V_{GS} = 10 V$ | $I_D = 30 \text{ A}, \text{T}_\text{J} = 125 \ ^\circ\text{C}$ | - | - | 0.0064 | Ω | |
| Drain-Source On-State Resistance | R _{DS(on)} | V _{GS} = 10 V | I _D = 30 A, T _J = 175 °C | - | - | 0.0080 | | |
| | | $V_{GS} = 4.5 V$ | I _D = 20 A | - | 0.0031 | 0.0039 | 1 | |
| Forward Transconductanceb | 9 _{fs} | V _{DS} = 15 V, I _D = 30 A | | - | 190 | - | S | |
| Dynamic ^b | | | | | | | | |
| Input Capacitance | C _{iss} | | | - | 11 755 | 14 700 | | |
| Output Capacitance | C _{oss} | $V_{GS} = 0 V$ | _S = 0 V V _{DS} = 25 V, f = 1 MHz | | 1112 | 1400 | pF | |
| Reverse Transfer Capacitance | C _{rss} | | | - | 481 | 605 | 1 | |
| Total Gate Charge ^c | Qg | | | - | 220 | 330 | nC | |
| Gate-Source Charge ^c | Q _{gs} | V _{GS} = 10 V | $V_{DS} = 30 \text{ V}, I_{D} = 110 \text{ A}$ | - | 35 | - | | |
| Gate-Drain Charge ^c | Q _{gd} | | 1 [| | 35 | - | 1 | |
| Gate Resistance | R _g | f = 1 MHz | | 0.6 | 1.3 | 2 | Ω | |
| Turn-On Delay Time ^c | t _{d(on)} | | | - | 19 | 29 | | |
| Rise Time ^c | t _r | $\label{eq:VDD} \begin{array}{l} V_{DD}=30~\text{V},~\text{R}_{\text{L}}=0.27~\Omega\\ \text{I}_{\text{D}}\cong110~\text{A},~\text{V}_{\text{GEN}}=10~\text{V},~\text{R}_{\text{g}}=2.5~\Omega \end{array}$ | | - | 23 | 35 | ns | |
| Turn-Off Delay Time ^c | t _{d(off)} | | | - | 83 | 125 | | |
| Fall Time ^c | t _f | | | - | 35 | 53 | | |
| Source-Drain Diode Ratings and Char | acteristics ^b | | | | • | | | |
| Pulsed Current ^a | I _{SM} | | | - | - | 480 | Α | |
| Forward Voltage | V _{SD} | I _F : | = 50 A, V _{GS} = 0 | - | 0.8 | 1.5 | V | |
| | | | | | | | | |

Notes

a. Pulse test; pulse width $\leq 300~\mu s,~duty~cycle \leq 2~\%.$

b. Guaranteed by design, not subject to production testing.

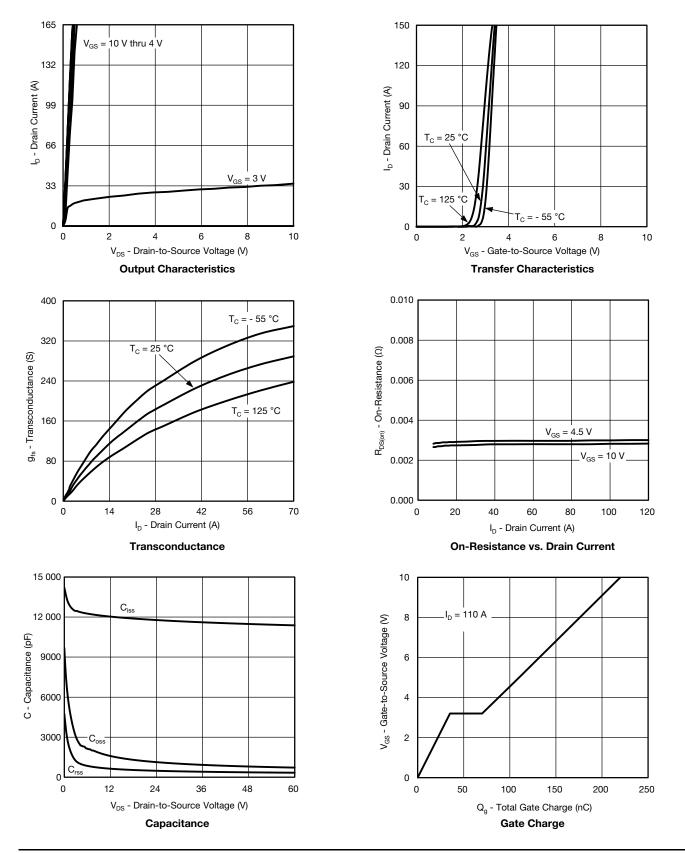
c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.





TYPICAL CHARACTERISTICS ($T_A = 25 \text{ °C}$, unless otherwise noted)



S13-2117-Rev. A, 07-Oct-13

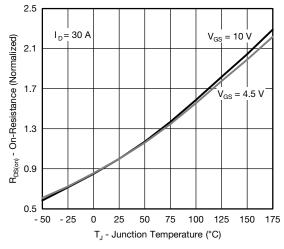
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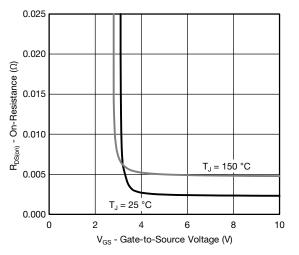
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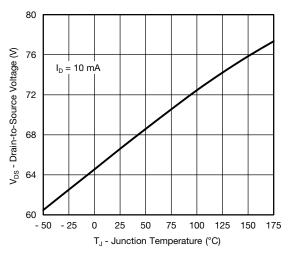
TYPICAL CHARACTERISTICS ($T_A = 25 \text{ °C}$, unless otherwise noted)







On-Resistance vs. Gate-to-Source Voltage

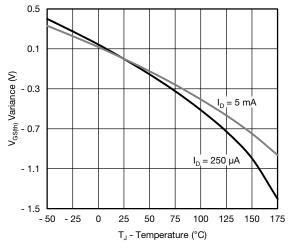


Drain Source Breakdown vs. Junction Temperature

T_J = 150 10 I_s - Source Current (A) 1 T_J = 25 °C 0.1 0.01 0.001 0.0 0.2 0.4 0.6 0.8 1.0 1.2 V_{SD} - Source-to-Drain Voltage (V)

100

Source Drain Diode Forward Voltage



Threshold Voltage

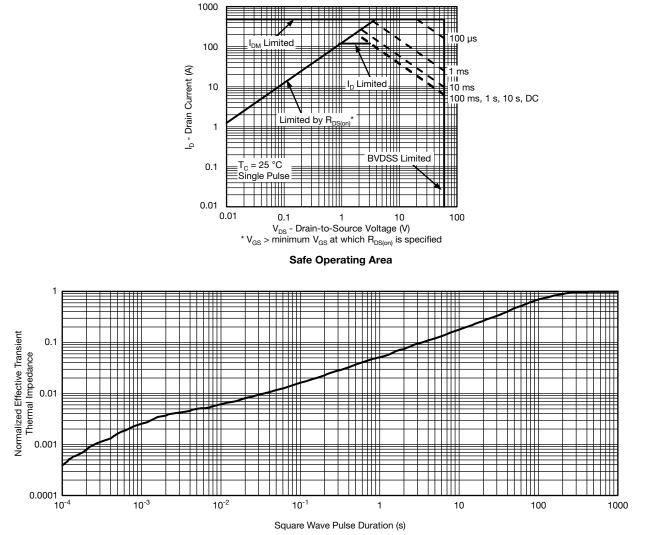
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THERMAL RATINGS ($T_A = 25 \text{ °C}$, unless otherwise noted)

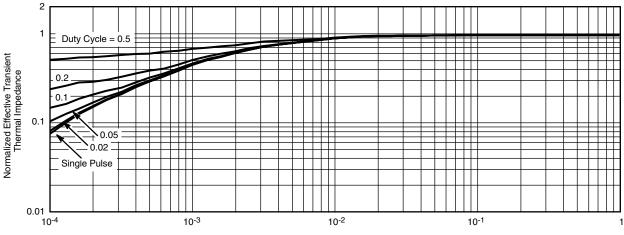


Normalized Thermal Transient Impedance, Junction-to-Ambient

5



THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Square Wave Pulse Duration (s)

Normalized Thermal Transient Impedance, Junction-to-Case

Note

· The characteristics shown in the two graphs

- Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)

- Normalized Transient Thermal Impedance Junction-to-Case (25 °C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?63814.

6



TO-263 (D²PAK): 3-LEAD









DETAIL A (ROTATED 90°)



| | | INCHES | | MILLIMETERS | | |
|--|------------|-----------|-------|-------------|--------|--|
| DIM. | | MIN. | MAX. | MIN. | MAX. | |
| А | | 0.160 | 0.190 | 4.064 | 4.826 | |
| | b | 0.020 | 0.039 | 0.508 | 0.990 | |
| | b1 | 0.020 | 0.035 | 0.508 | 0.889 | |
| | b2 | 0.045 | 0.055 | 1.143 | 1.397 | |
| с* | Thin lead | 0.013 | 0.018 | 0.330 | 0.457 | |
| C | Thick lead | 0.023 | 0.028 | 0.584 | 0.711 | |
| c1 | Thin lead | 0.013 | 0.017 | 0.330 | 0.431 | |
| CI | Thick lead | 0.023 | 0.027 | 0.584 | 0.685 | |
| | c2 | 0.045 | 0.055 | 1.143 | 1.397 | |
| | D | 0.340 | 0.380 | 8.636 | 9.652 | |
| | D1 | 0.220 | 0.240 | 5.588 | 6.096 | |
| | D2 | 0.038 | 0.042 | 0.965 | 1.067 | |
| | D3 | 0.045 | 0.055 | 1.143 | 1.397 | |
| D4 | | 0.044 | 0.052 | 1.118 | 1.321 | |
| | E | 0.380 | 0.410 | 9.652 | 10.414 | |
| | E1 | 0.245 | - | 6.223 | - | |
| | E2 | 0.355 | 0.375 | 9.017 | 9.525 | |
| E3 | | 0.072 | 0.078 | 1.829 | 1.981 | |
| | е | 0.100 BSC | | 2.54 BSC | | |
| | К | 0.045 | 0.055 | 1.143 | 1.397 | |
| L | | 0.575 | 0.625 | 14.605 | 15.875 | |
| L1 | | 0.090 | 0.110 | 2.286 | 2.794 | |
| L2 | | 0.040 | 0.055 | 1.016 | 1.397 | |
| L3 | | 0.050 | 0.070 | 1.270 | 1.778 | |
| L4 | | 0.010 BSC | | 0.254 BSC | | |
| М | | - | 0.002 | - | 0.050 | |
| ECN: T13-0707-Rev. K, 30-Sep-13 DWG: 5843 | | | | | | |

Notes

- 1. Plane B includes maximum features of heat sink tab and plastic. 2. No more than 25 % of L1 can fall above seating plane by
- max. 8 mils.3. Pin-to-pin coplanarity max. 4 mils.
- 4. *: Thin lead is for SUB, SYB.
 - Thick lead is for SUM, SYM, SQM.
- 5. Use inches as the primary measurement.

This feature is for thick lead.

Revison: 30-Sep-13



RECOMMENDED MINIMUM PADS FOR D²PAK: 3-Lead



Recommended Minimum Pads Dimensions in Inches/(mm)

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